# SKKT 27B08 E G6

**SEMIPACK® 1**

## Thyristor Modules

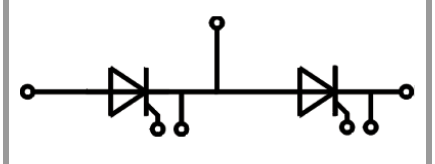
**SKKT 27B08 E G6**

### Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E63532

### Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)



**SKKT**

| Absolute Maximum Ratings | | | | |
|---|---|---|---|---|
| **Symbol** | **Conditions** | | **Values** | **Unit** |
| **Chip** | | | | |
| $I_{T(AV)}$ | sinus 180° | $T_c$ = 85 °C | 28 | A |
| | | $T_c$ = 100 °C | 21 | A |
| $I_{TSM}$ | 10 ms | $T_j$ = 25 °C | 550 | A |
| | | $T_j$ = 130 °C | 480 | A |
| $i^2t$ | 10 ms | $T_j$ = 25 °C | 1513 | $kA^2s$ |
| $i^2t$ | | $T_j$ = 130 °C | 1152 | $kA^2s$ |
| $V_{RSM}$ | | | 900 | V |
| $V_{RRM}$ | | | 800 | V |
| $V_{DRM}$ | | | 800 | V |
| $(di/dt)_{cr}$ | $T_j$ = 130 °C | | 140 | A/µs |
| $(dv/dt)_{cr}$ | $T_j$ = 130 °C | | 1000 | V/µs |
| $T_j$ | | | -40 ... 130 | °C |
| **Module** | | | | |
| $T_{stg}$ | | | -40 ... 125 | °C |
| $V_{isol}$ | a.c.; 50 Hz; r.m.s. | 1 min | 3000 | V |
| | | 1 s | 3600 | V |

| Characteristics | | | | | | |
|---|---|---|---|---|---|---|
| **Symbol** | **Conditions** | | **min.** | **typ.** | **max.** | **Unit** |
| **Chip** | | | | | | |
| $V_T$ | $T_j$ = 25 °C, $I_T$ = 75 A | | | 1.45 | 1.7 | V |
| $V_{T(TO)}$ | $T_j$ = 130 °C | | | 0.85 | 1 | V |
| $r_T$ | $T_j$ = 130 °C | | | 8.50 | 10.00 | mΩ |
| $I_{DD}$;$I_{RD}$ | $T_j$ = 130 °C, $V_{DD}$ = $V_{DRM}$; $V_{RD}$ = $V_{RRM}$ | | | | 20 | mA |
| $t_{gd}$ | $T_j$ = 25 °C, $I_G$ = 1 A, $di_G/dt$ = 1 A/µs | | | 1 | | µs |
| $t_{gr}$ | $V_D$ = 0.67 * $V_{DRM}$ | | | 2 | | µs |
| $t_q$ | $T_j$ = 130 °C | | | 150 | | µs |
| $I_H$ | $T_j$ = 25 °C | | | 150 | 250 | mA |
| $I_L$ | $T_j$ = 25 °C, $R_G$ = 33 Ω | | | 300 | 600 | mA |
| $V_{GT}$ | $T_j$ = 25 °C, d.c. | | 2.5 | | | V |
| $I_{GT}$ | $T_j$ = 25 °C, d.c. | | 100 | | | mA |
| $V_{GD}$ | $T_j$ = 130 °C, d.c. | | | | 0.25 | V |
| $I_{GD}$ | $T_j$ = 130 °C, d.c. | | | | 4 | mA |
| $R_{th(j-c)}$ | cont. | per chip | | | 0.880 | K/W |
| | | per module | | | 0.440 | K/W |
| $R_{th(j-c)}$ | sin. 180° | per chip | | | 0.930 | K/W |
| | | per module | | | 0.465 | K/W |
| $R_{th(j-c)}$ | rec. 120° | per chip | | | 0.980 | K/W |
| | | per module | | | 0.490 | K/W |
| **Module** | | | | | | |
| $R_{th(c-s)}$ | chip | | | 0.22 | | K/W |
| | module | | | 0.11 | | K/W |
| $M_s$ | to heatsink M5 | | 4.25 | | 5.75 | Nm |
| $M_t$ | to terminals M5 | | 2.55 | | 3.45 | Nm |
| a | | | | | 5 * 9,81 | $m/s^2$ |
| w | | | | 75 | | g |

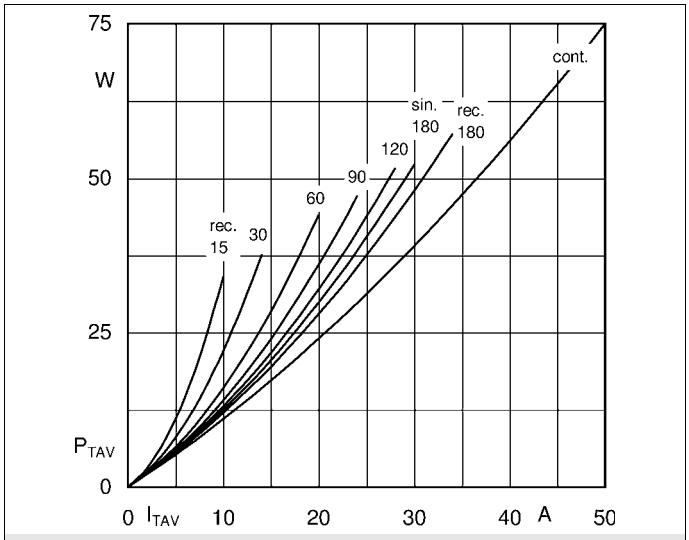



Fig. 1L: Max. power dissipation per chip vs. on-state current

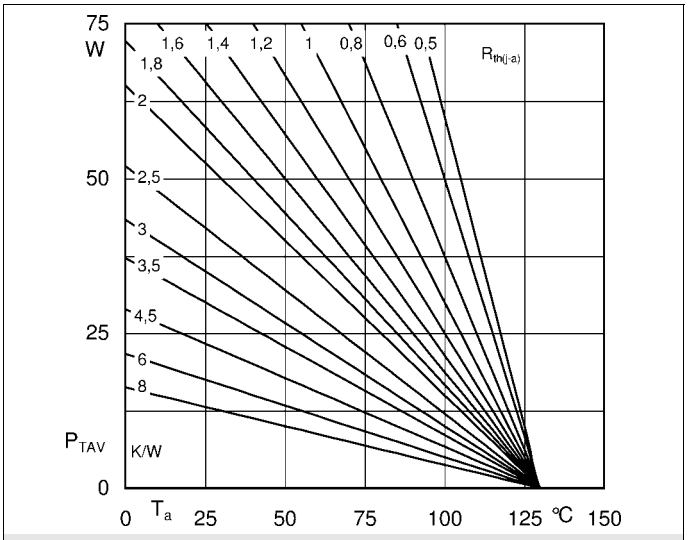



Fig. 1R: Max. power dissipation per chip vs. ambient temperature

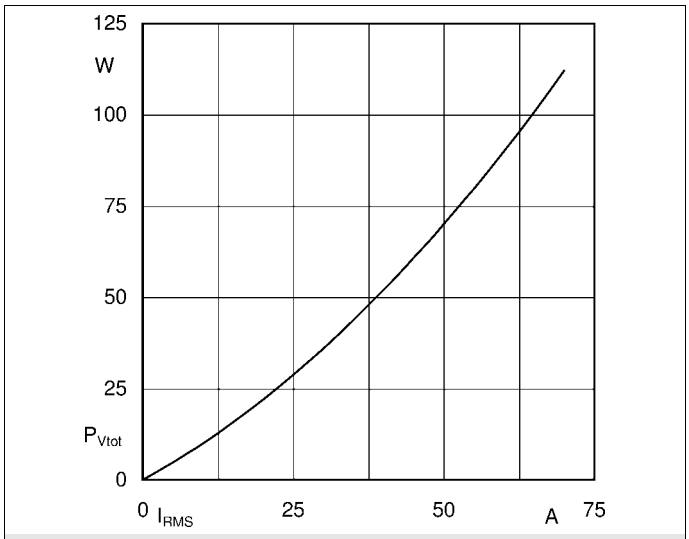



Fig. 2L: Max. power dissipation of one module vs. rms current

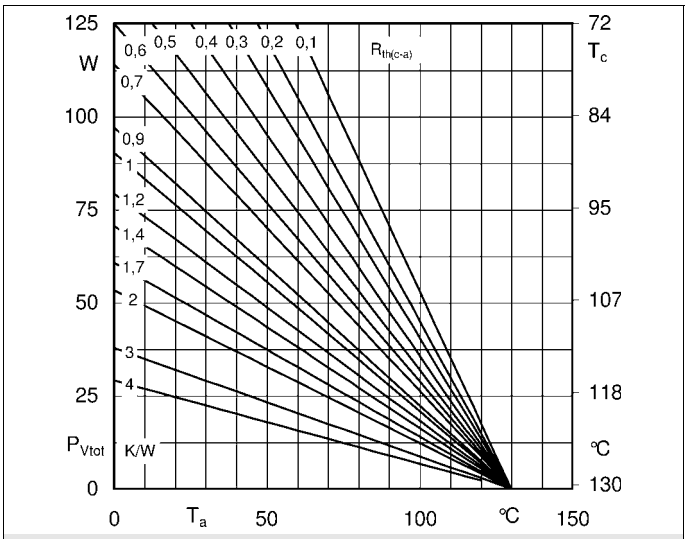



Fig. 2R: Max. power dissipation of one module vs. case temperature

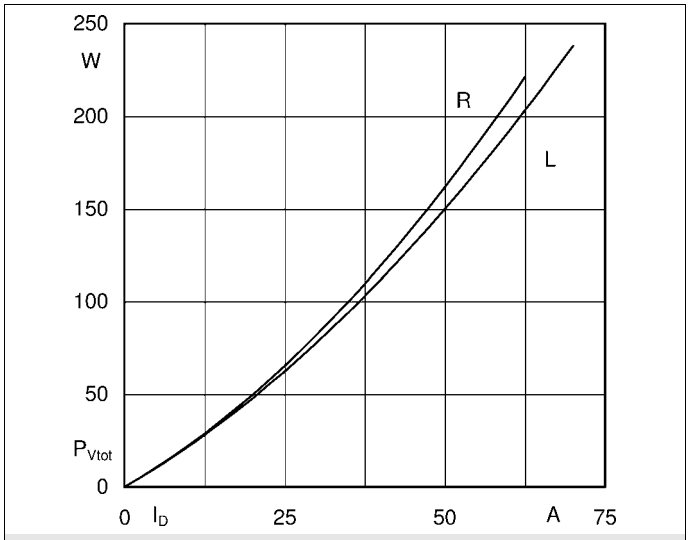



Fig. 3L: Max. power dissipation of two modules vs. direct current

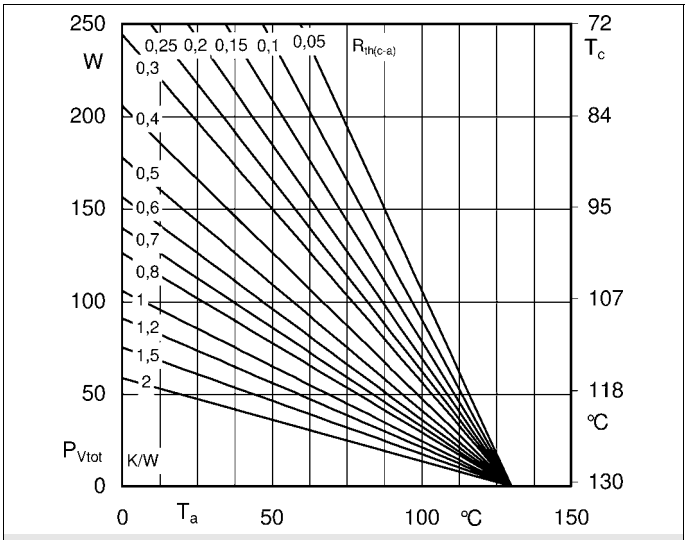



Fig. 3R: Max. power dissipation of two modules vs. case temperature

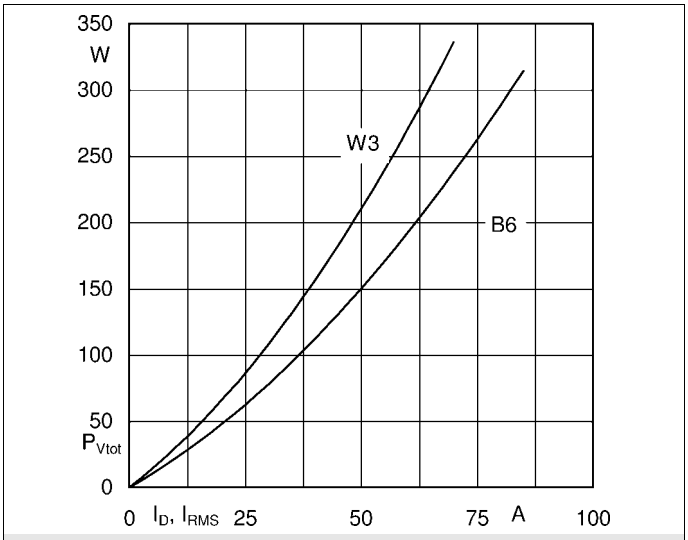



Fig. 4L: Max. power dissipation of three modules vs. direct current

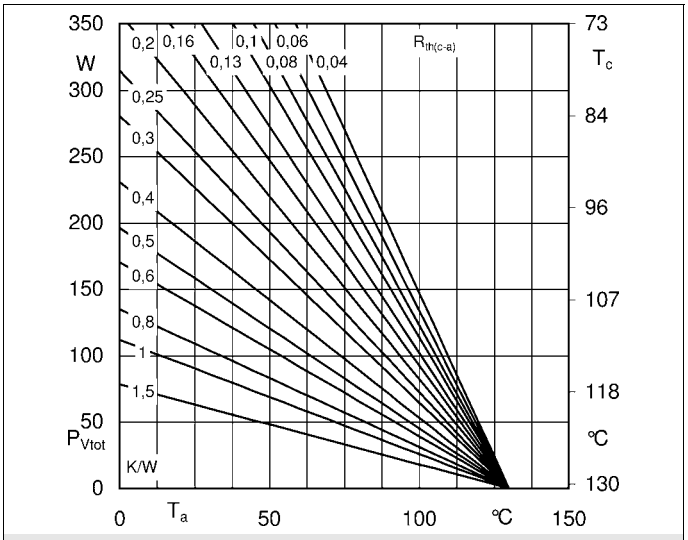



Fig. 4R: Max. power dissipation of three modules vs. case temperature

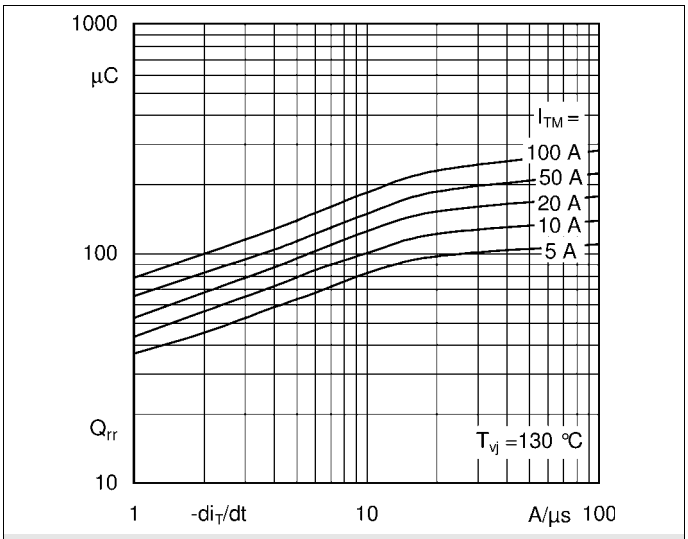



Fig. 5: Recovered charge vs. current decrease

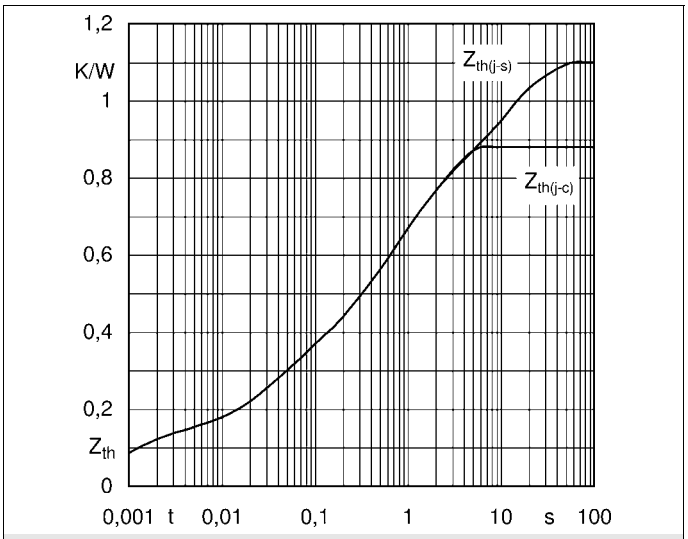



Fig. 6: Transient thermal impedance vs. time

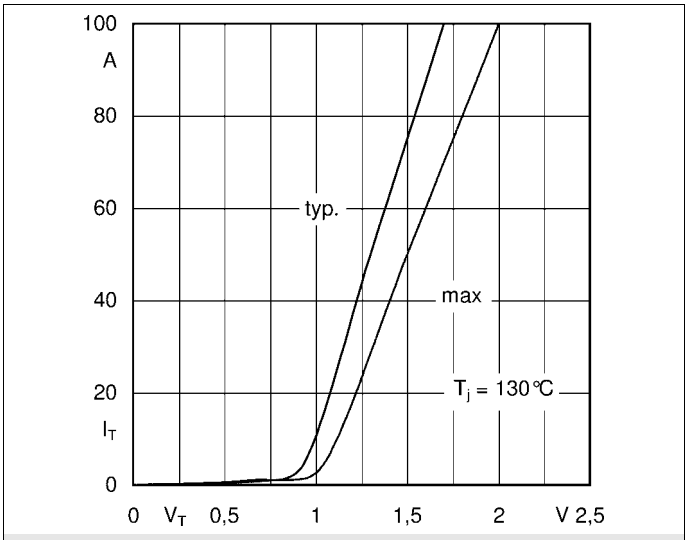



Fig. 7: On-state characteristics

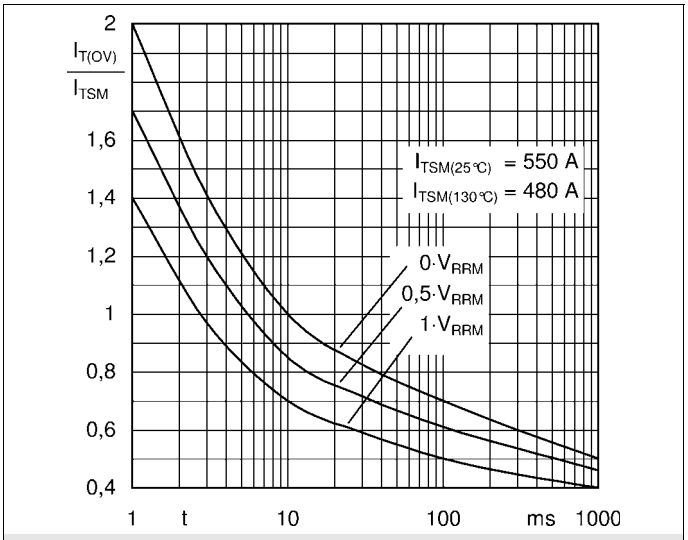



Fig. 8: Surge overload current vs. time

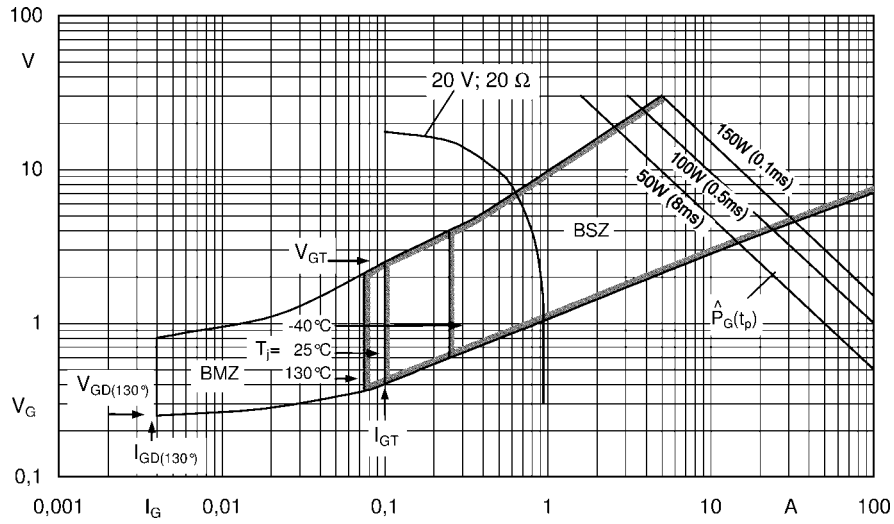
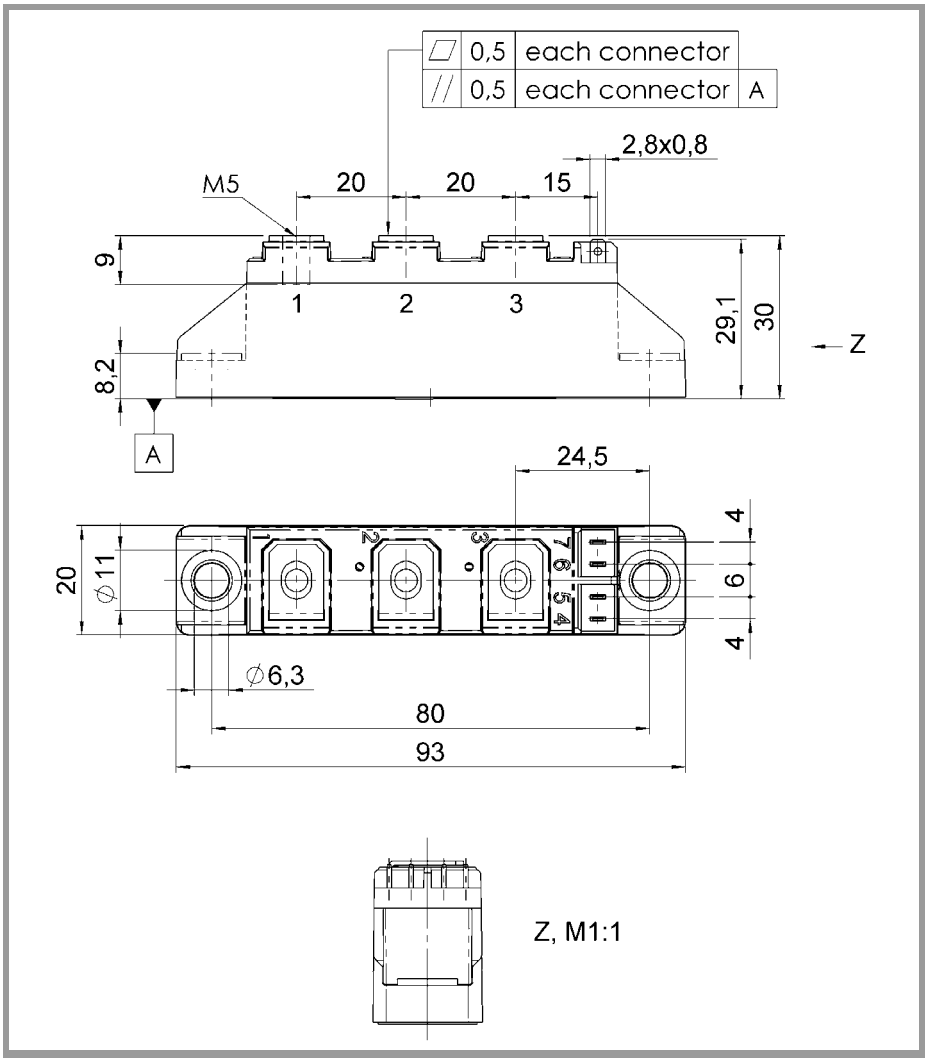
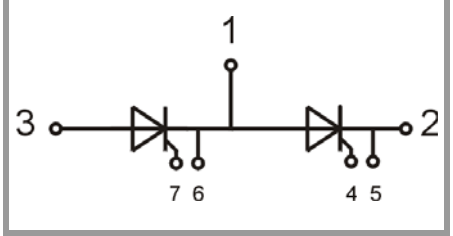



Fig. 9: Gate trigger characteristics




SEMIPACK 1




SKKT...B

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.